

isc N-Channel MOSFET Transistor

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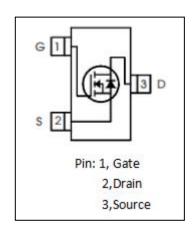
• FEATURES

- Low drain-source on-resistance: R_Ds(on) ≤45mΩ
- · Fast Switching Speed
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



• DESCRITION

 Provides the designer with an extremely efficient and reliable device for use in battery and load management.



• ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER		UNIT
V _{DSS}	Drain-Source Voltage	20	V
V _{GS}	Gate-Source Voltage	±12	V
I _D	Drain Current-Continuous	4.2	А
I _{DM}	Drain Current-Single Pulsed	33	А
P _D	Total Dissipation @T _C =25℃	1.25	W
Tj	Max. Operating Junction Temperature	150	$^{\circ}$ C
T _{stg}	Storage Temperature	-55~150	°C

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
Rth(ch-a)	Channel-to-ambient thermal resistance		°C/W



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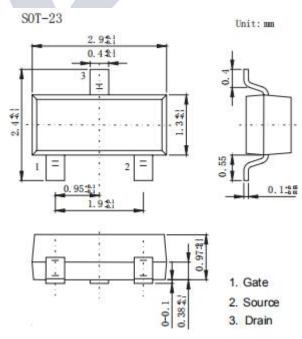
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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	MAX	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; ID =250 μ A	20			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} ; ID =250 μ A	0.6		1.2	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =4.5V; I _D =4.2A			0.045	- Ω
		V _{GS} =2.5V; I _D =3.6A			0.08	
I _{GSS}	Gate-Source Leakage Current	V _{GS} = ±12V			±100	nA
I _{DSS}	Drain-Source Leakage Current	V _{DS} =16V; V _{GS} = 0V			1	- μΑ
		V _{DS} =16V; V _{GS} = 0V; T _j = 70°C			25	
V _{SD}	Diode forward voltage	I _S =1.3A; V _{GS} = 0V			1.2	V

OUTLINE DRAWING





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